

2N3904

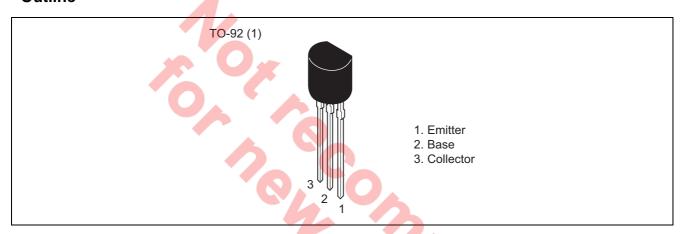
Silicon NPN Epitaxial General Purpose Amplifier

REA03G0001-0200Z Rev.2.00 Jul.22.2004

Features

- Low saturation voltage
- General purpose amplifier and switching
- The useful dynamic range extends to 100mA as a switch and to 100MHz as an amplifier

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

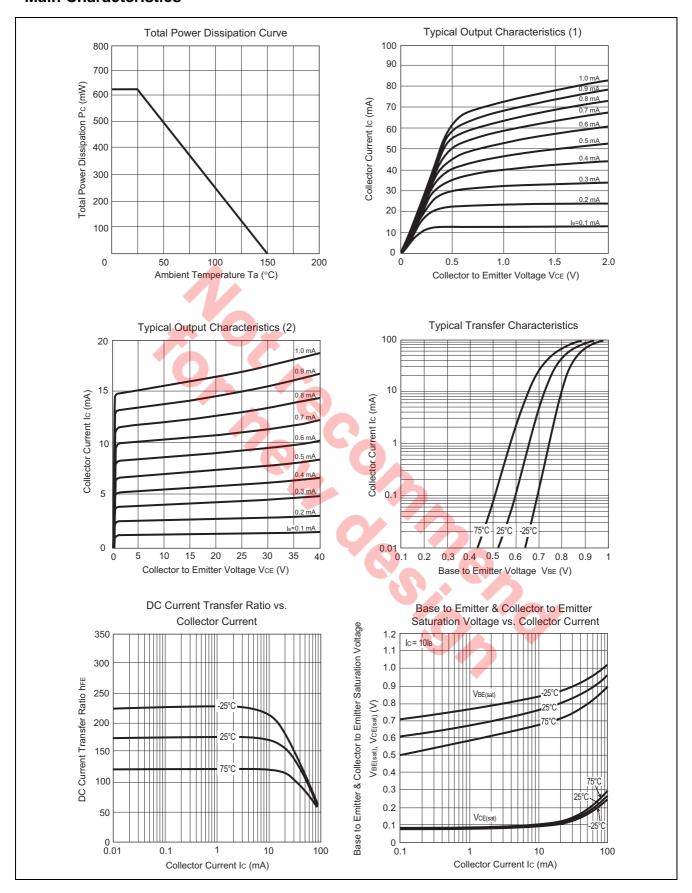
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	60	V
Collector to emitter voltage	V _{CEO}	40	V
Emitter to base voltage	V _{EBO}	6	V
Collector current	Ic	200	mA
Total power dissipation	Pc	625	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

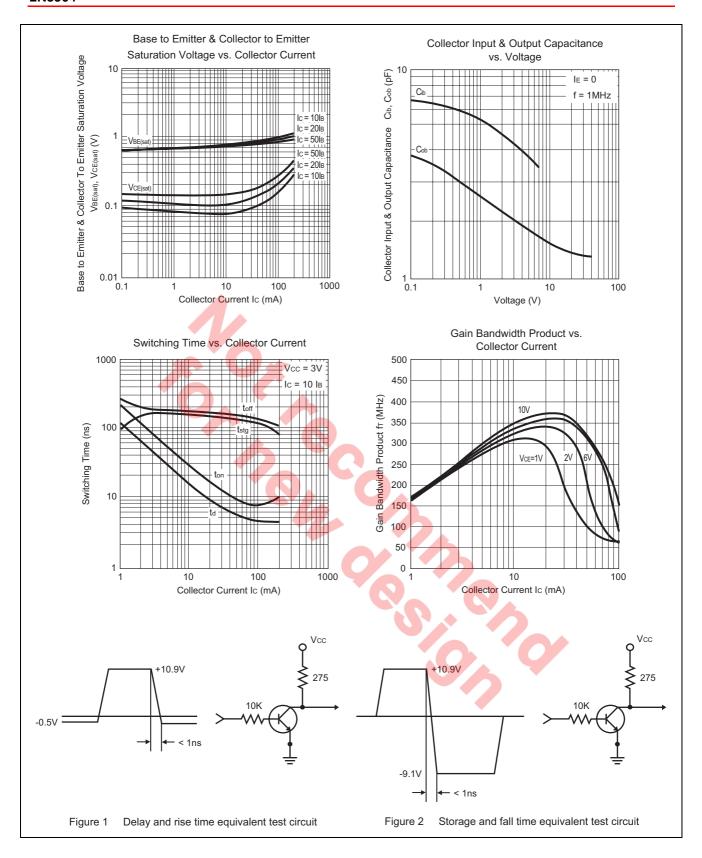
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

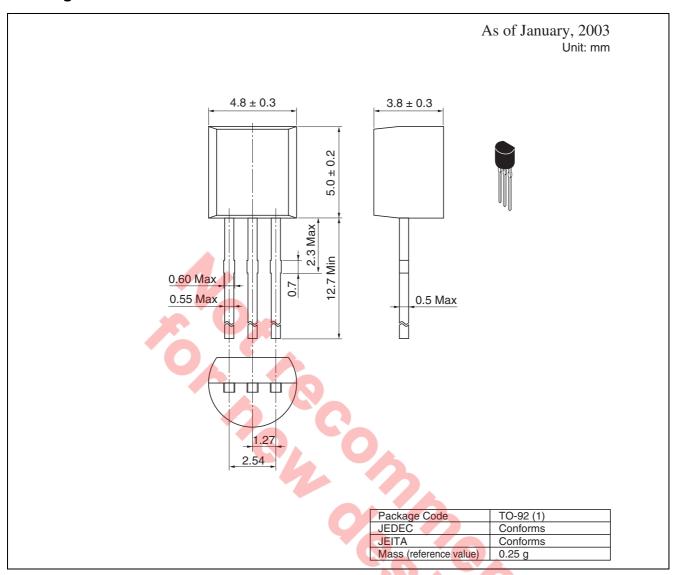
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	_	_	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	40	_	<u> </u>	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	_	<u> </u>	V	$I_E = 10 \mu A, I_C = 0$
Base cutoff current	I _{BL}	_	_	50	nA	V _{CE} = 30 V, V _{EB} = 3 V
Collector cutoff current	I _{CEX}	_	_	50	nA	V _{CE} = 30 V, V _{EB} = 3 V
DC current transfer ratio	h _{FE}	40	_	T-	_	$V_{CE} = 1 \text{ V}, I_{C} = 100 \mu\text{A}$
		70	_	_	_	$V_{CE} = 1 \text{ V}, I_{C} = 1 \text{ mA}$
		100	_	300	_	$V_{CE} = 1 \text{ V}, I_{C} = 10 \text{ mA}$
		60	_	_	_	$V_{CE} = 1 \text{ V}, I_{B} = 50 \text{ mA}$
		30	_	_	_	$V_{CE} = 1 \text{ V}, I_{B} = 100 \text{ mA}$
Collector to emitter saturation voltage	V _{CE(sat)}	_	_	0.2	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
		_	_	0.3	V	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$
Base to emitter saturation voltage	V _{BE(sat)}	0.65	_	0.85	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
		_	_	0.95	V	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$
Gain bandwidth product	f _T	_	540	_	MHz	V _{CE} = 20 V, I _C = 10 mA
Collector output capacitance	C _{ob}	_	1.9	1 —	pF	$V_{CE} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Collector input capacitance	C _{ib}	_	5.9	1 —	pF	V _{CE} = 0.5 V, I _E = 0, f = 1 MHz
Noise figure	NF		1.0	1_	dB	
						$f = 1 \text{ MHz}, R_g = 1 \text{ k}\Omega$
	C	2	0	2		
			4			
				10		A
			`			
Noise figure NF $=$ 1.0 $=$ dB $V_{CE} = 5 \text{ V}$, $I_C = 0.1 \text{ mA}$, $I_C = 1 \text{ MHz}$, $I_C = 0.1 \text{ mA}$, $I_C = 1 \text{ MHz}$						

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2N3904	2500pcs	Radial Taping (Hold Box)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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